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AUSTRIA



ELD-1060-525

- **INFRARED** Light Emitting Diode
- **1060 nm, 11 mW**
- **AlGaAs, MQW**
- **5 mm epoxy package**



Description

ELD-1060-525 is an **AlGaAs MQW** infrared LED, typically emitting at 1060 nm with an optical output power of 1.6 mW. It comes in a hermetically sealed clear 5 mm epoxy resin. **ELD-1060-525** is commonly used for optical communication and automation.

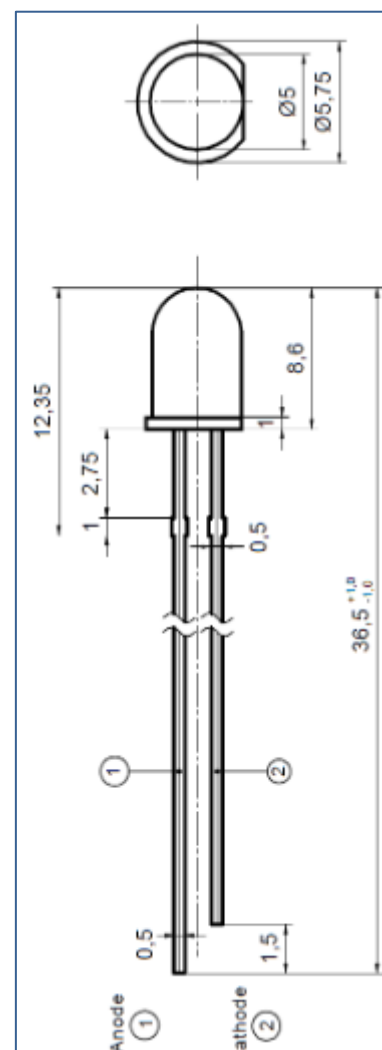
Maximum Rating ($T_{CASE} = 25^{\circ}C$)

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation, DC	P_D		150	mW
Forward Current	I_{FM}		100	mA
Pulse Forward Current*	I_{FP}		200	mA
Operating Temperature	T_{OPR}	- 20	+ 80	$^{\circ}C$
Storage Temperature	T_{STG}	- 55	+ 85	$^{\circ}C$
Soldering Temperature (max 3s)	T_{SOL}		+ 260	$^{\circ}C$
Junction Temperature	T_J		/	$^{\circ}C$

* $t_p \leq 50 \mu s$, $t_p/T = 1/2$

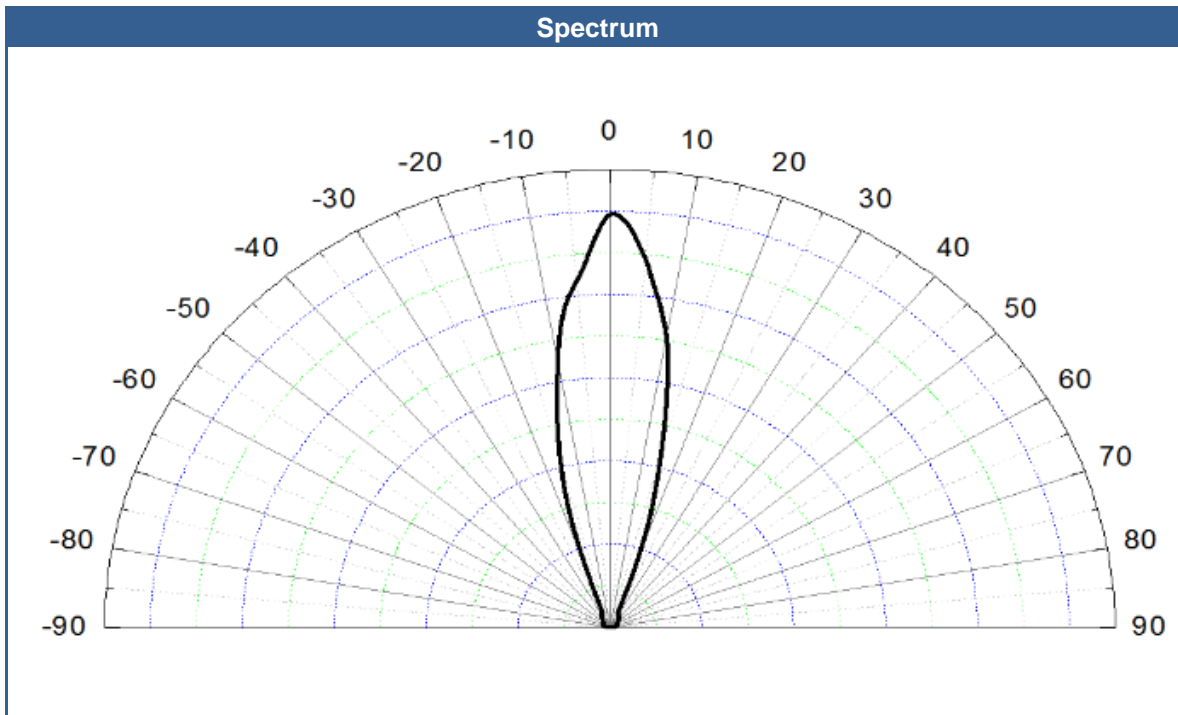
Electro-Optical Characteristics ($T_{CASE} = 25^{\circ}C$, $I_F = 20 \text{ mA}$)

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Peak Wavelength	λ_P	1040	1060	1080	nm
Spectral Width (FWHM)	$\Delta\lambda$		80		nm
Forward Voltage @ 20 mA	V_F		1.15	1.4	V
Forward Voltage @ 100 mA	V_F		1.25	1.5	V
Reverse Voltage ($I_R = 10 \mu A$)	V_R	5			V
Radiant Power @ 20 mA	Θ_e		1.6		mW
Radiant Power @ 100 mA	Θ_e		8		mW
Switching time	t_R, t_F		20		ns
Viewing Half Angle	$\Theta_{1/2}$		10		deg.





Performance Characteristics ($T_{CASE} = 25^{\circ}C$)



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